β-Ga₂O₃ Epitaxial Wafers and Substrates

 β -Ga₂O₃ is a new semiconductor material for power devices and has larger band-gap energy than SiC and GaN. Therefore, It will likely be used to make that can withstand high voltages and low resistance semiconductors. In addition, since growing β -Ga₂O₃ single crystal from a melt it is possible to provide high quality substrates with low cost compared with SiC and GaN to the market.



Contact details for inquiries



Novel Crystal Technology, Inc.

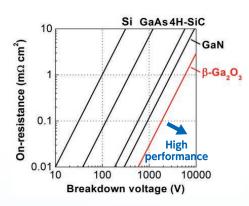
2-3-1 Hirosedai Sayama-shi Saitama 350-1328 TEL.+81-4-2900-0072 FAX.+81-4-2900-0059 http://www.novelcrystal.co.jp/ mail:sales@novelcrystal.co.jp

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Characteristics of β-Ga₂O₃

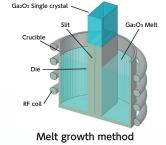
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Relationship between theoretical on-resistance and breakdown voltage

	SiC, GaN	β-Ga 2 O 3
Growth rate	Slow	Fast
Substrate process	Difficult	Easy





Reasons for low cost of β-Ga₂O₃

Applications

Power Electronics



Electric vehicles



Railroad vehicles



Renewable energy



Smart Grid

Devices in extreme environment



Nuclear reactors (radiation)



Space (radiation, electromagnetic waves)

Other applications



High-sensitivity image sensors



Scintillators (medical , security)



Ultraviolet sensors

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